



PATENT
1592-0131P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Shigeto FUJIMURA et al. Conf.: Unknown
Appl. No.: 09/753,662 Group: Unknown
Filed: January 4, 2001 Examiner: Unknown
For: PROCESS FOR PRODUCING COMPOUND
SEMICONDUCTOR SINGLE CRYSTAL

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

April 3, 2001

RECEIVED
APR - 3 2001
TECHNOLOGY CENTER 1700

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE SPECIFICATION

✓
Please replace the paragraph beginning on page 5, line 8, with the following rewritten paragraph:

2₁
--According to the report (M. Muhlberg et al., Journal of Crystal Growth, Vol. 128, (1993) pp 571-575), when a deviation between a temperature at which a supercooled liquid is solidified and the melting point of the supercooled liquid is defined as a degree of supercooling, the degree of supercooling is correlated with a holding temperature of the melt. In the concrete, it is reported that the degree of supercooling becomes low when a difference between a temperature at which the raw material is held